

MAC210A8, MAC210A10





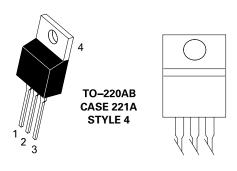
Description

Designed primarily for full-wave AC control applications, such as light dimmers, motor controls, heating controls and power supplies; or wherever full-wave silicon gate controlled solid-state devices are needed. Triac type thyristors switch from a blocking to a conducting state for either polarity of applied main terminal voltage with positive or negative gate triggering.

Features

- Blocking Voltage to 600 Volts
- All Diffused and Glass Passivated Junctions for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Gate Triggering Guaranteed in Four Modes (Quadrants)
- Pb-Free Packages are Available

Pin Out



Functional Diagram



Additional Information







Resources



Samples



Maximum Ratings $(T_1 = 25^{\circ}C \text{ unless otherwise noted})$

Rating	Symbol	Value	Unit	
Peak Repetitive Off-State Voltage (Note 1) MAC210A8 (- 40 to 125°C, Sine Wave, 50 to 60 Hz, Gate Open) MAC210A10		V _{DRM} , V _{RRM}	600 800	V
On-State RMS Current (Full Cycle Sine Wave, 50 to 60 Hz, $T_c = 70$ °C)		I _{T (RMS)}	10	А
Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, $T_c = +25$ °C) Preceded and followed by rated current		I _{TSM}	100	А
Circuit Fusing Consideration (t = 8.3 ms)	l²t	40	A²sec	
Peak Gate Power ($T_c = +80^{\circ}\text{C}$, Pulse Width = 1.0 μ s)	P_{GM}	20	W	
Average Gate Power (t = 8.3 ms , $T_c = 80^{\circ}\text{C}$)	P _{G (AV)}	0.35	W	
Peak Gate Current (T _c = +70°C, Pulse Width = 10 s)	I _{GM}	2.0	А	
Operating Junction Temperature Range		T _J	-40 to +125	°C
Storage Temperature Range		T _{stg}	-40 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are

Thermal Characteristics

Rating		Symbol	Value	Unit
Thermal Resistance,	Junction-to-Case (AC) Junction-to-Ambient	R _{ejc} R _{eja}	2.0 62.5	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 10 seconds		T _L	260	°C

Electrical Characteristics - **OFF** $(T_j = 25^{\circ}\text{C unless otherwise noted}; Electricals apply in both directions)$

Characteristic		Symbol	Min	Тур	Max	Unit
Peak Repetitive Blocking Current	T ₁ = 25°C	I _{DRM} ,	-	-	1.0	A
$(V_D = V_{DRM} = V_{RRM}; Gate Open)$	$T_J = 125^{\circ}C$	IRRM	-	-	2.0	mA

Electrical Characteristics - ON (T₁ = 25°C unless otherwise noted; Electricals apply in both directions)

Characteristic		Symbol	Min	Тур	Max	Unit
Peak On-State Voltage (TM = 14 A Peak; Pulse Width = 1 to 2 ms, Duty Cycle 2%)		V _{TM}	_	_	1.6	V
	MT2(+), G(+)		_	12	50	mA
Gate Trigger Current	MT2(+), G(-)		_	12	50	
(Continuous dc) $(V_D = 12 \text{ V}, R_L = 100 \text{ Ohms})$	MT2(-), G(-)	GT GT	_	20	50	
	MT2(-), G(+)		_	35	75	
Gate Trigger Voltage (Continuous dc) ($V_D = 12 \text{ V}, \text{ R}_L = 100 \Omega$)	MT2(+), G(+)	V _{GT}	_	0.9	2.0	
	MT2(+), G(-)		_	0.9	2.0	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \
	MT2(-), G(-)		_	1.1	2.0	V
	MT2(-), G(+)		_	1.4	2.5	
Holding Current ($V_D = 12 V_{dc'}$ Gate Open, Initiating Current = ±150 mA))		I _H	-	6.0	50	mA
Turn-On Time (Rated $V_{DRM'}$ $I_{TM} = 14 \text{ A}$) ($I_{CT} = 120 \text{ mA}$, Rise Time = 0.1 s, Pulse Width = 2 s)		t _{gt}	_	1.5	_	μs

not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

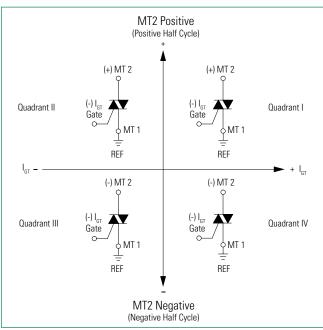


Dynamic Characteristics Characteristic Symbol Min Max Unit Тур Critical Rate of Rise of Commutation Voltage (di/dt)c 5.0 A/ms $(V_D = Rated V_{DRM'} I_{TM} = 14 A$, Commutating di/dt = 5.0 A/ms, Gate Unenergized, TC = 70°C) Critical Rate of Rise of Off-State Voltage V/µs dv/dt 100 $(V_D = Rated V_{DRM}, Exponential Waveform, Gate Open, T_C = +70°C)$

Voltage Current Characteristic of SCR

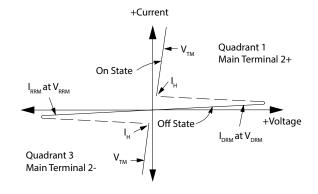
Symbol	Parameter
V _{DRM}	Peak Repetitive Forward Off State Voltage
I	Peak Forward Blocking Current
V _{RRM}	Peak Repetitive Reverse Off State Voltage
I _{RRM}	Peak Reverse Blocking Current
V_{TM}	Maximum On State Voltage
I _H	Holding Current

Quadrant Definitions for a Triac



All Polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used



Thyristors



Figure 1. Current Derating

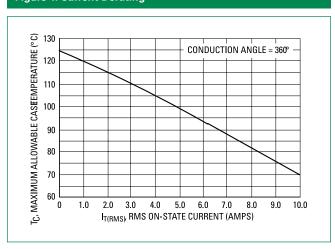


Figure 3. Maximum On-State Characteristics

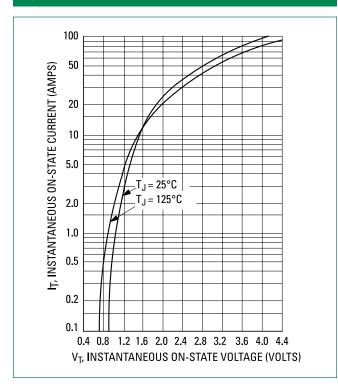


Figure 2. Power Dissipation

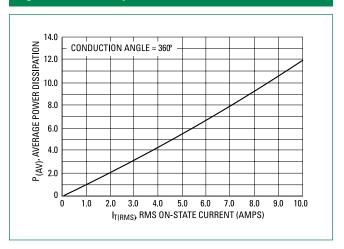


Figure 4. Maximum Non-Repetitive Surge Current

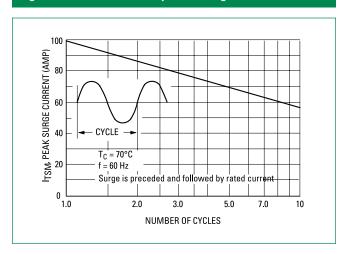


Figure 5. Typical Gate Trigger Voltage

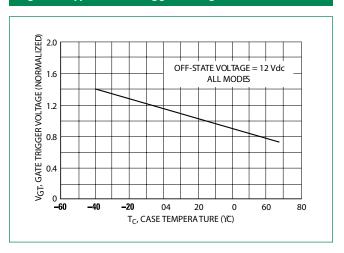




Figure 6. Typical Gate Trigger Current

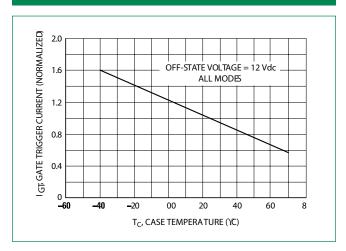
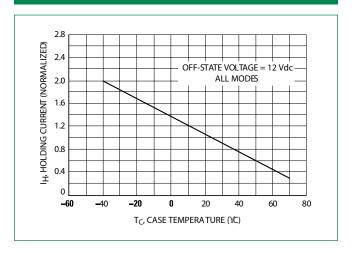


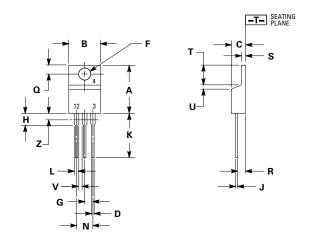
Figure 7. Typical Holding Current





Surface Mount - 400V - 800V > MAC210A8, MAC210A10

Dimensions



Part Marking System







X	=8 or 10
Υ	=Year
M	=Month
Α	=Assembly Site
XX	=Lot Serial Code
G	=Pb-Free Package

D:	Inc	hes	Millimeters		
Dim	Min	Max	Min	Max	
Α	0.590	0.620	14.99	15.75	
В	0.380	0.420	9.65	10.67	
С	0.178	0.188	4.52	4.78	
D	0.025	0.035	0.64	0.89	
F	0.142	0.147	3.61	3.73	
G	0.095	0.105	2.41	2.67	
Н	0.110	0.130	2.79	3.30	
J	0.018	0.024	0.46	0.61	
K	0.540	0.575	13.72	14.61	
L	0.060	0.075	1.52	1.91	
N	0.195	0.205	4.95	5.21	
Q	0.105	0.115	2.67	2.92	
R	0.085	0.095	2.16	2.41	
S	0.045	0.060	1.14	1.52	
Т	0.235	0.255	5.97	6.47	
U	0.000	0.050	0.00	1.27	
V	0.045		1.15		
Z		0.080		2.04	

Pin Assignment			
1	Main Terminal 1		
2	Main Terminal 2		
3	Gate		
4	No Connection		

Ordering Information					
Device	Package	Shipping			
MAC210A8	TO-220AB				
MAC210A8G	TO-220AB (Pb-Free)	500			
MAC210A10	TO-220AB	Units/ Box			
MAC210A10G	TO-220AB (Pb-Free)				

^{1.} DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

^{2.} CONTROLLING DIMENSION: INCH.

DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.